









SN74AHC1G14-Q1

SCLS956A - AUGUST 2023 - REVISED OCTOBER 2023

SN74AHC1G14-Q1 Automotive Single Schmitt-Trigger Inverter Gate

1 Features

- AEC-Q100 qualified for automotive applications:
 - Device temperature grade 1: -40°C to +125°C
 - Device HBM ESD classification level 2
 - Device CDM ESD classification level C4B
- Operating range of 2-V to 5.5-V
- Low power consumption, 10-µA maximum I_{CC}
- ±8-mA output drive at 5 V
- Latch-up performance exceeds 250 mA per JESD 17

2 Applications

- Synchronize inverted clock inputs
- Debounce a switch
- Invert a digital signal

3 Description

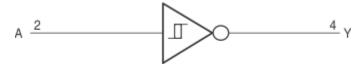
The SN74AHC1G14-Q1 is a single inverter gate. The device performs the Boolean function $Y = \overline{A}$.

The device functions as an independent inverter gate, but because of the Schmitt action, gates may have different input threshold levels for positive-going (V_{T+}) and negative-going (V_T_) signals.

Package Information

PART NUMBER	PACKAGE ⁽¹⁾	PACKAGE SIZE(2)	BODY SIZE(3)
SN74AHC1G14-Q1	DBV (SOT-23, 5)	2.9 mm x 2.8 mm	2.9 mm x 1.6 mm
31174A11C1G14-Q1	DCK (SC70, 5)	2 mm × 2.1 mm	2 mm × 1.25 mm

- For all available packages, see the orderable addendum at the end of the data sheet.
- The package size (length × width) is a nominal value and includes pins, where applicable.
- The body size (length × width) is a nominal value and does not include pins.



Simplified Logic Diagram (Positive Logic)



Table of Contents

1 Features	1	8.3 Feature Description	9
2 Applications		8.4 Device Functional Modes	
3 Description		9 Application and Implementation	11
4 Revision History		9.1 Application Information	
5 Pin Configuration and Functions		9.2 Typical Application	
6 Specifications		9.3 Power Supply Recommendations	13
6.1 Absolute Maximum Ratings		9.4 Layout	13
6.2 ESD Ratings		10 Device and Documentation Support	
6.3 Recommended Operating Conditions	4	10.1 Documentation Support	15
6.4 Thermal Information	5	10.2 Receiving Notification of Documentation Updates	s 15
6.5 Electrical Characteristics	5	10.3 Support Resources	15
6.6 Switching Characteristics	6	10.4 Trademarks	15
6.7 Typical Characteristics	7	10.5 Electrostatic Discharge Caution	15
7 Parameter Measurement Information		10.6 Glossary	
8 Detailed Description	9	11 Mechanical, Packaging, and Orderable	
8.1 Overview	9	Information	15
8.2 Functional Block Diagram			
8.2 Functional Block Diagram	9		

4 Revision History

C	hanges from Revision * (August 2023) to Revision A (October 2023)	Page
•	Added DBV package to Package Information table	1
•	Added DBV package to Pin Configuration and Functions section	3
•	Added thermal values for DBV package: RθJA = 278.0, RθJC(top) = 180.5, RθJB = 184.4, ΨJT = 115.4	ŧ, ΨJB
	= 183.4, RθJC(bot) = N/A, all values in °C/W	5

Product Folder Links: SN74AHC1G14-Q1



5 Pin Configuration and Functions

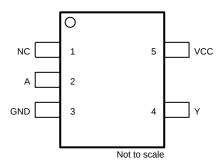


Figure 5-1. SN74AHC1G14-Q1 DBV Package, 5-Pin SOT-23; DCK Package, 5-Pin SC-70 (Top View)

Table 5-1. Pin Functions

Р	IN	TYPE ⁽¹⁾	DESCRIPTION					
NAME	NO.	1176	DESCRIPTION					
NC	1	I	No Connect					
Α	2	I	Input					
GND	3	G	Ground					
Υ	4	0	Output					
V _{CC}	5	Р	Power Supply					

(1) I = input, O = output, I/O = input or output, G = ground, P = power.



6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
V _{CC}	Supply voltage		-0.5	7	V
VI	Input voltage range	nput voltage range		7	V
Vo	Output voltage range	Output voltage range		V _{CC} + 0.5	V
Vo		Voltage range applied to any output in the high-impedance or power-off state		4.6	V
I _{IK}	Input clamp current ⁽²⁾	V ₁ < 0	-20		mA
I _{OK}	Output clamp current ⁽²⁾	$V_O < 0$ or $V_O > V_{CC}$	-20	20	mA
Io	Continuous output current	V _O = 0 to V _{CC}	-25	25	mA
I _O	Continuous output current through	n V _{CC} or GND	-50	50	mA
T _J	Junction temperature			150	°C
T _{stg}	Storage temperature		-65	150	°C

⁽¹⁾ Operation outside the Absolute Maximum Ratings may cause permanent device damage. Absolute maximum ratings do not imply functional operation of the device at these or any other conditions beyond those listed under Recommended Operating Conditions. If briefly operating outside the Recommended Operating Conditions but within the Absolute Maximum Ratings, the device may not sustain damage, but it may not be fully functional. Operating the device in this manner may affect device reliability, functionality, performance, and shorten the device lifetime.

(2) The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

6.2 ESD Ratings

			VALU E	UNIT
V _(ESD) Electrostatic discharge	Human body model (HBM), per AEC Q100-002 ⁽¹⁾ HBM ESD Classification Level 2	±200 0	V	
V _(ESD)	Electrostatic discharge	Charged device model (CDM), per AEC Q100-011 CDM ESD Classification Level C4B	±100 0	V

⁽¹⁾ AEC Q100-002 indicate that HBM stressing shall be in accordance with the ANSI/ESDA/JEDEC JS-001 specification.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	MAX	UNIT
V _{CC}	Supply Voltage		2	5.5	V
		V _{CC} = 2 V	1.5		V
V _{IH}	high-level input voltage	V _{CC} = 3V	2.1		V
		V _{CC} = 5.5 V	3.85		V
		V _{CC} = 2 V		0.5	V
V _{IL}	low-level input voltage	V _{CC} = 3 V		0.9	V
		V _{CC} = 5.5 V		1.65	V
VI	input voltage		0	5.5	V
V _O	output voltage		0	V _{CC}	V
		V _{CC} = 2 V		-50	μA
I _{OH}	high-level output current	V _{CC} = 3.3 V ± 0.3 V		-4	mA
		V _{CC} = 5 V ± 0.5 V		-8	mA
		V _{CC} = 2 V		50	μA
I _{OL}	low-level output current	V _{CC} = 3.3 V ± 0.3 V		4	mA
		V _{CC} = 5 V ± 0.5 V		8	mA

Submit Document Feedback

Copyright © 2023 Texas Instruments Incorporated



6.3 Recommended Operating Conditions (continued)

over operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	MAX	UNIT
Δt/Δν	input transition rise or fall rate	$V_{CC} = 3.3 \text{ V} \pm 0.3$		100	nS/V
Δt/Δν	input transition rise or fall rate	$V_{CC} = 5 V \pm 0.5 V$		20	nS/V
T _A	Operating free-air temperature		-55	125	°C

6.4 Thermal Information

		SN74AH0		
	THERMAL METRIC ⁽¹⁾	DBV (SOT-23)	DCK (SC70)	UNIT
		5 PINS	5 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	278.0	293.4	°C/W
R _{0JC(top)}	Junction-to-case (top) thermal resistance	180.5	208.8	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	184.4	180.6	°C/W
Ψ_{JT}	Junction-to-top characterization parameter	115.4	120.6	°C/W
Ψ_{JB}	Junction-to-board characterization parameter	183.4	179.5	°C/W
R _{0JC(bot)}	Junction-to-case (bottom) thermal resistance	N/A	N/A	°C/W

⁽¹⁾ For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

6.5 Electrical Characteristics

over operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V	T	= 25°C	-40°(UNIT	
PARAMETER	TEST CONDITIONS	V _{cc}	MIN	TYP MAX	MIN	TYP MAX	UNIT
		Vcc = 3 V	1.2	2.20	1.2	2.20	V
V_{T+}	Positive-going input threshold voltage	Vcc = 4.5 V	1.75	3.15	1.75	3.15	V
	unosnola voltago	Vcc = 5.5 V	2.15	3.85	2.15	3.85	V
V _{T-}		Vcc = 3 V	0.9	1.9	0.9	1.9	V
	Negative-going input threshold voltage	Vcc = 4.5 V	1.35	2.75	1.35	2.75	V
	l	Vcc = 5.5 V	1.65	3.35	1.65	3.35	V
ΔV_{T}		Vcc = 3 V	0.3	1.2	0.3	1.2	V
	Hysteresis (V _{T+} - V _{T-})	Vcc = 4.5 V	0.4	1.4	0.4	1.4	V
		Vcc = 5.5 V	0.5	1.6	0.5	1.6	V
	I _{OH} = -50 μA	Vcc = 2 V	1.9		1.9		V
	I _{OH} = -50 μA	Vcc = 3 V	2.9		2.9		V
V _{OH}	I _{OH} = –50 μA	Vcc = 4.5 V	4.4		4.4		V
	I _{OH} = –4 mA	Vcc = 3 V	2.58		2.48		V
	I _{OH} = –8 mA	Vcc = 4.5 V	3.94		3.8		V
	I _{OH} = 50 μA	Vcc = 2 V		0.1		0.1	V
	I _{OH} = 50 μA	Vcc = 3 V		0.1		0.1	V
V _{OL}	I _{OH} = 50 μA	Vcc = 4.5 V		0.1		0.1	V
	I _{OH} = 4 mA	Vcc = 3 V		0.36		0.44	V
	I _{OH} = 8 mA	Vcc = 4.5 V		0.36		0.44	V
I _I	V _I = 5.5V or GND	0 V to 5.5 V	-0.1	0.1	-1	1	μΑ
I _{CC}	$V_I = V_{CC}$ or GND, $I_O = 0$	5.5 V		1		4	μΑ
Ci	V _I = V _{CC} or GND	5 V		1.7 10			pF
Co	V _O = V _{CC} or GND	5 V		3			pF

Copyright © 2023 Texas Instruments Incorporated

Submit Document Feedback



6.5 Electrical Characteristics (continued)

over operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V	T _A = 25°C			-40°C to 125°C			UNIT
FARAWIETER	TEST CONDITIONS	V _{cc}	MIN	TYP	MAX	MIN	TYP	MAX	UNIT
C _{PD}	Power dissipation capacitance	5 V		14					pF

6.6 Switching Characteristics

over operating free-air temperature range (unless otherwise noted)

PARAMETER	FROM	то	LOAD	V	T	= 25°	С	-40°	C to 85°C	-40°0	C to 125°	С	UNIT
PARAWETER	(INPUT)	(OUTPUT)	CAPACITANCE	V _{CC}	MIN	TYP	MAX	MIN	TYP MAX	MIN	TYP M	AX	UNIT
T _{PLH}	Α	Υ	CL = 15 pF	3.3 V ± 0.3 V		5	7.1	1	8.5	1		9.5	ns
T _{PHL}	Α	Y	CL = 15 pF	3.3 V ± 0.3 V		5	7.1	1	8.5	1		9.5	ns
T _{PLH}	Α	Y	CL = 50 pF	3.3 V ± 0.3 V		7.5	10.6	1	12	1		13	ns
T _{PHL}	Α	Y	CL = 50 pF	3.3 V ± 0.3 V		7.5	10.6	1	12	1		13	ns
T _{PLH}	Α	Y	CL = 15 pF	5 V ± 0.5 V		3.6	5.5	1	6.5	1		7	ns
T _{PHL}	Α	Y	CL = 15 pF	5 V ± 0.5 V		3.6	5.5	1	6.5	1	•	7	ns
T _{PLH}	Α	Υ	CL = 50 pF	5 V ± 0.5 V		5.1	7.5	1	6.5	1		7	ns
T _{PHL}	Α	Υ	CL = 50 pF	5 V ± 0.5 V		5.1	7.5	1	6.5	1		7	ns

Product Folder Links: SN74AHC1G14-Q1



6.7 Typical Characteristics

T_A = 25°C (unless otherwise noted)

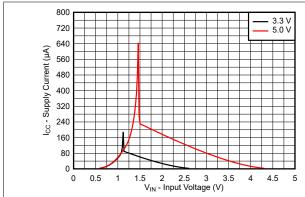


Figure 6-1. Supply Current Across Input Voltage 3.3-V and 5.0-V Supply

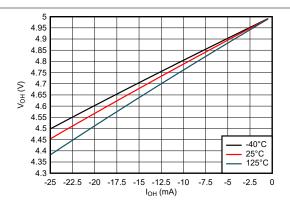


Figure 6-2. Output Voltage vs Current in HIGH State; 5-V Supply

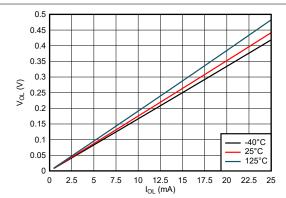


Figure 6-3. Output Voltage vs Current in LOW State; 5-V Supply

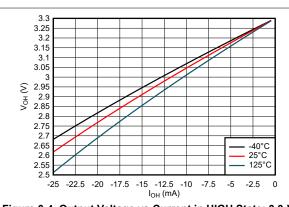


Figure 6-4. Output Voltage vs Current in HIGH State; 3.3-V Supply

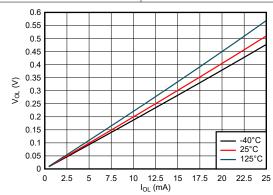


Figure 6-5. Output Voltage vs Current in LOW State; 3.3-V Supply

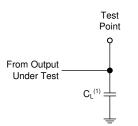


7 Parameter Measurement Information

Phase relationships between waveforms were chosen arbitrarily. All input pulses are supplied by generators having the following characteristics: PRR \leq 1 MHz, Z_O = 50 Ω .

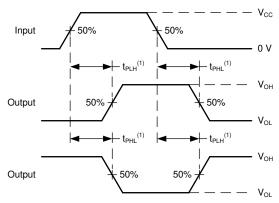
For clock inputs, f_{max} is measured when the input duty cycle is 50%.

The outputs are measured one at a time with one input transition per measurement.



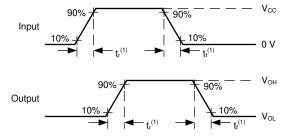
(1) C_L includes probe and test-fixture capacitance.

Figure 7-1. Load Circuit for Push-Pull Outputs



(1) The greater between t_{PLH} and t_{PHL} is the same as $t_{\text{pd}}.$

Figure 7-2. Voltage Waveforms Propagation Delays



(1) The greater between t_{r} and t_{f} is the same as t_{t} .

Figure 7-3. Voltage Waveforms, Input and Output Transition Times

Submit Document Feedback

Copyright © 2023 Texas Instruments Incorporated

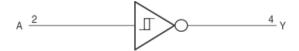
8 Detailed Description

8.1 Overview

The SN74AHC1G14-Q1 is a single inverter gate. The device performs the Boolean function $Y = \overline{A}$.

The device functions as an independent inverter gate, but because of the Schmitt action, gates may have different input threshold levels for positive-going (V_{T+}) and negative-going (V_{T-}) signals.

8.2 Functional Block Diagram



8.3 Feature Description

8.3.1 CMOS Schmitt-Trigger Inputs

This device includes inputs with the Schmitt-trigger architecture. These inputs are high impedance and are typically modeled as a resistor in parallel with the input capacitance given in the *Electrical Characteristics* table from the input to ground. The worst case resistance is calculated with the maximum input voltage, given in the *Absolute Maximum Ratings* table, and the maximum input leakage current, given in the *Electrical Characteristics* table, using Ohm's law ($R = V \div I$).

The Schmitt-trigger input architecture provides hysteresis as defined by ΔV_T in the *Electrical Characteristics* table, which makes this device extremely tolerant to slow or noisy inputs. While the inputs can be driven much slower than standard CMOS inputs, it is still recommended to properly terminate unused inputs. Driving the inputs with slow transitioning signals will increase dynamic current consumption of the device. For additional information regarding Schmitt-trigger inputs, please see *Understanding Schmitt Triggers*.

8.3.2 Balanced CMOS Push-Pull Outputs

This device includes balanced CMOS push-pull outputs. The term *balanced* indicates that the device can sink and source similar currents. The drive capability of this device may create fast edges into light loads, so routing and load conditions should be considered to prevent ringing. Additionally, the outputs of this device are capable of driving larger currents than the device can sustain without being damaged. It is important for the output power of the device to be limited to avoid damage due to overcurrent. The electrical and thermal limits defined in the *Absolute Maximum Ratings* must be followed at all times.

Unused push-pull CMOS outputs should be left disconnected.



8.3.3 Clamp Diode Structure

The outputs to this device have both positive and negative clamping diodes, and the inputs to this device have negative clamping diodes only as shown in Figure 8-1.

CAUTION

Voltages beyond the values specified in the *Absolute Maximum Ratings* table can cause damage to the device. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

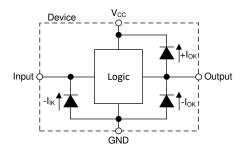


Figure 8-1. Electrical Placement of Clamping Diodes for Each Input and Output

8.4 Device Functional Modes

Table 8-1 lists the functional modes of the SN74AHC1G14-Q1.

Table 8-1. Function Table

INPUT ⁽¹⁾ A	OUTPUT Y
Н	L
L	Н

(1) H = high voltage level, L = low voltage level

Submit Document Feedback

Copyright © 2023 Texas Instruments Incorporated



9 Application and Implementation

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

9.1 Application Information

The SN74AHC1G14-Q1can be used to add an additional stage to a counter with an external flip-flop. Because counters use a negative edge trigger, the flip-flop's clock input must be inverted to provide this function. Having Schmitt-trigger inputs is important in this application to eliminate any noise issues that could impact the counting function which could lead to incorrect frequency division.

The SN74AHC1G14-Q1 is a high drive CMOS device that can be used for implementing inversion logic with a high output drive.

9.2 Typical Application

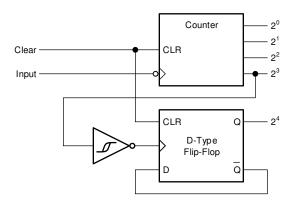


Figure 9-1. Typical Application Block Diagram

9.2.1 Design Requirements

9.2.1.1 Power Considerations

Ensure the desired supply voltage is within the range specified in the *Recommended Operating Conditions*. The supply voltage sets the electrical characteristics of the device as described in the *Electrical Characteristics* section.

The positive voltage supply must be capable of sourcing current equal to the total current to be sourced by all outputs of the SN74AHC1G14-Q1 plus the maximum static supply current, I_{CC} , listed in the *Electrical Characteristics*, and any transient current required for switching. The logic device can only source as much current that is provided by the positive supply source. Be sure to not exceed the maximum total current through V_{CC} listed in the *Absolute Maximum Ratings*.

The ground must be capable of sinking current equal to the total current to be sunk by all outputs of the SN74AHC1G14-Q1 plus the maximum supply current, I_{CC}, listed in the *Electrical Characteristics*, and any transient current required for switching. The logic device can only sink as much current that can be sunk into its ground connection. Be sure to not exceed the maximum total current through GND listed in the *Absolute Maximum Ratings*.

The SN74AHC1G14-Q1 can drive a load with a total capacitance less than or equal to 50 pF while still meeting all of the data sheet specifications. Larger capacitive loads can be applied; however, it is not recommended to exceed 50 pF.



The SN74AHC1G14-Q1 can drive a load with total resistance described by $R_1 \ge V_0 / I_0$, with the output voltage and current defined in the Electrical Characteristics table with VOH and VOL. When outputting in the HIGH state, the output voltage in the equation is defined as the difference between the measured output voltage and the supply voltage at the V_{CC} pin.

Total power consumption can be calculated using the information provided in the CMOS Power Consumption and Cpd Calculation application note.

Thermal increase can be calculated using the information provided in the *Thermal Characteristics of Standard* Linear and Logic (SLL) Packages and Devices application note.

CAUTION

The maximum junction temperature, $T_{J(max)}$ listed in the Absolute Maximum Ratings, is an additional limitation to prevent damage to the device. Do not violate any values listed in the Absolute Maximum Ratings. These limits are provided to prevent damage to the device.

9.2.1.2 Input Considerations

Input signals must cross $V_{t-(min)}$ to be considered a logic LOW, and $V_{t+(max)}$ to be considered a logic HIGH. Do not exceed the maximum input voltage range found in the Absolute Maximum Ratings.

Unused inputs must be terminated to either V_{CC} or ground. The unused inputs can be directly terminated if the input is completely unused, or they can be connected with a pull-up or pull-down resistor if the input will be used sometimes, but not always. A pull-up resistor is used for a default state of HIGH, and a pull-down resistor is used for a default state of LOW. The drive current of the controller, leakage current into the SN74AHC1G14-Q1 (as specified in the *Electrical Characteristics*), and the desired input transition rate limits the resistor size. A 10-k Ω resistor value is often used due to these factors.

The SN74AHC1G14-Q1 has no input signal transition rate requirements because it has Schmitt-trigger inputs.

Another benefit to having Schmitt-trigger inputs is the ability to reject noise. Noise with a large enough amplitude can still cause issues. To know how much noise is too much, please refer to the $\Delta V_{T(min)}$ in the *Electrical* Characteristics. This hysteresis value will provide the peak-to-peak limit.

Unlike what happens with standard CMOS inputs, Schmitt-trigger inputs can be held at any valid value without causing huge increases in power consumption. The typical additional current caused by holding an input at a value other than V_{CC} or ground is plotted in the *Typical Characteristics*.

Refer to the *Feature Description* section for additional information regarding the inputs for this device.

9.2.1.3 Output Considerations

The positive supply voltage is used to produce the output HIGH voltage. Drawing current from the output will decrease the output voltage as specified by the V_{OH} specification in the Electrical Characteristics. The ground voltage is used to produce the output LOW voltage. Sinking current into the output will increase the output voltage as specified by the V_{OL} specification in the *Electrical Characteristics*.

Push-pull outputs that could be in opposite states, even for a very short time period, should never be connected directly together. This can cause excessive current and damage to the device.

Two channels within the same device with the same input signals can be connected in parallel for additional output drive strength.

Unused outputs can be left floating. Do not connect outputs directly to V_{CC} or ground.

Refer to the Feature Description section for additional information regarding the outputs for this device.

9.2.2 Detailed Design Procedure

 Add a decoupling capacitor from V_{CC} to GND. The capacitor needs to be placed physically close to the device and electrically close to both the V_{CC} and GND pins. An example layout is shown in the Layout section.

Product Folder Links: SN74AHC1G14-Q1

www.ti.com

- 2. Ensure the capacitive load at the output is ≤ 50 pF. This is not a hard limit; by design, however, it will optimize performance. This can be accomplished by providing short, appropriately sized traces from the SN74AHC1G14-Q1 to one or more of the receiving devices.
- 3. Ensure the resistive load at the output is larger than $(V_{CC} / I_{O(max)}) \Omega$. Doing this will prevent the maximum output current from the Absolute Maximum Ratings from being violated. Most CMOS inputs have a resistive load measured in $M\Omega$; much larger than the minimum calculated previously.
- 4. Thermal issues are rarely a concern for logic gates; the power consumption and thermal increase, however, can be calculated using the steps provided in the application report, CMOS Power Consumption and Cpd Calculation.

9.2.3 Application Curves

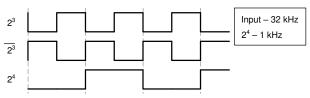


Figure 9-2. Application Timing Diagram

9.3 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in the Recommended Operating Conditions. Each V_{CC} terminal should have a good bypass capacitor to prevent power disturbance. A 0.1-µF capacitor is recommended for this device. It is acceptable to parallel multiple bypass capacitors to reject different frequencies of noise. The 0.1-µF and 1-µF capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power terminal as possible for best results, as shown in the following layout example.

9.4 Layout

9.4.1 Layout Guidelines

When using multiple-input and multiple-channel logic devices, inputs must never be left floating. In many cases, functions or parts of functions of digital logic devices are unused (for example, when only two inputs of a triple-input AND gate are used or only 3 of the 4 buffer gates are used). Such unused input pins must not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. All unused inputs of digital logic devices must be connected to a logic high or logic low voltage, as defined by the input voltage specifications, to prevent them from floating. The logic level that must be applied to any particular unused input depends on the function of the device. Generally, the inputs are tied to GND or V_{CC}, whichever makes more sense for the logic function or is more convenient.



9.4.2 Layout Example

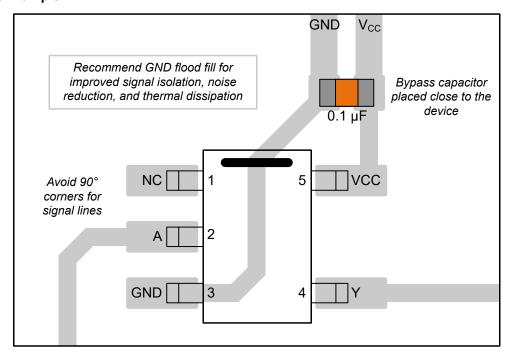


Figure 9-3. Example Layout for the SN74AHC1G14-Q1



10 Device and Documentation Support

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed below.

10.1 Documentation Support

10.1.1 Related Documentation

For related documentation, see the following:

- Texas Instruments, CMOS Power Consumption and Cpd Calculation application note
- Texas Instruments, Designing With Logic application note
- Texas Instruments, Thermal Characteristics of Standard Linear and Logic (SLL) Packages and Devices application note
- Texas Instruments, Implications of Slow or Floating CMOS Inputs application note

10.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Notifications* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

10.3 Support Resources

TI E2E™ support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

10.4 Trademarks

TI E2E™ is a trademark of Texas Instruments.

All trademarks are the property of their respective owners.

10.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

10.6 Glossary

TI Glossary

This glossary lists and explains terms, acronyms, and definitions.

11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

Copyright © 2023 Texas Instruments Incorporated

www.ti.com 7-Oct-2025

PACKAGING INFORMATION

Orderable part number	Status	Material type	Package Pins	Package qty Carrier	RoHS	Lead finish/ Ball material	MSL rating/ Peak reflow	Op temp (°C)	Part marking (6)
						(4)	(5)		
SN74AHC1G14QDBVRQ1	Active	Production	SOT-23 (DBV) 5	3000 LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	38TH
SN74AHC1G14QDBVRQ1.A	Active	Production	SOT-23 (DBV) 5	3000 LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	38TH
SN74AHC1G14QDCKRQ1	Active	Production	SC70 (DCK) 5	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	1QH
SN74AHC1G14QDCKRQ1.A	Active	Production	SC70 (DCK) 5	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	1QH

⁽¹⁾ Status: For more details on status, see our product life cycle.

- (3) RoHS values: Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.
- (4) Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.
- (5) MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.
- (6) Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

OTHER QUALIFIED VERSIONS OF SN74AHC1G14-Q1:

⁽²⁾ Material type: When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

PACKAGE OPTION ADDENDUM

www.ti.com 7-Oct-2025

● Catalog : SN74AHC1G14

NOTE: Qualified Version Definitions:

• Catalog - TI's standard catalog product

PACKAGE MATERIALS INFORMATION

www.ti.com 4-Nov-2023

TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	_	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74AHC1G14QDBVRQ1	SOT-23	DBV	5	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
SN74AHC1G14QDCKRQ1	SC70	DCK	5	3000	178.0	9.0	2.4	2.5	1.2	4.0	8.0	Q3

PACKAGE MATERIALS INFORMATION

www.ti.com 4-Nov-2023



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74AHC1G14QDBVRQ1	SOT-23	DBV	5	3000	210.0	185.0	35.0
SN74AHC1G14QDCKRQ1	SC70	DCK	5	3000	190.0	190.0	30.0





NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
 2. This drawing is subject to change without notice.
 3. Reference JEDEC MO-178.

- 4. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25 mm per side.
- 5. Support pin may differ or may not be present.





NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.





NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.







NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
 2. This drawing is subject to change without notice.
 3. Reference JEDEC MO-203.

- 4. Support pin may differ or may not be present.5. Lead width does not comply with JEDEC.
- 6. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25mm per side





NOTES: (continued)

7. Publication IPC-7351 may have alternate designs.8. Solder mask tolerances between and around signal pads can vary based on board fabrication site.





NOTES: (continued)

- 9. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 10. Board assembly site may have different recommendations for stencil design.



IMPORTANT NOTICE AND DISCLAIMER

TI PROVIDES TECHNICAL AND RELIABILITY DATA (INCLUDING DATA SHEETS), DESIGN RESOURCES (INCLUDING REFERENCE DESIGNS), APPLICATION OR OTHER DESIGN ADVICE, WEB TOOLS, SAFETY INFORMATION, AND OTHER RESOURCES "AS IS" AND WITH ALL FAULTS, AND DISCLAIMS ALL WARRANTIES, EXPRESS AND IMPLIED, INCLUDING WITHOUT LIMITATION ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS.

These resources are intended for skilled developers designing with TI products. You are solely responsible for (1) selecting the appropriate TI products for your application, (2) designing, validating and testing your application, and (3) ensuring your application meets applicable standards, and any other safety, security, regulatory or other requirements.

These resources are subject to change without notice. TI grants you permission to use these resources only for development of an application that uses the TI products described in the resource. Other reproduction and display of these resources is prohibited. No license is granted to any other TI intellectual property right or to any third party intellectual property right. TI disclaims responsibility for, and you will fully indemnify TI and its representatives against, any claims, damages, costs, losses, and liabilities arising out of your use of these resources.

TI's products are provided subject to TI's Terms of Sale or other applicable terms available either on ti.com or provided in conjunction with such TI products. TI's provision of these resources does not expand or otherwise alter TI's applicable warranties or warranty disclaimers for TI products.

TI objects to and rejects any additional or different terms you may have proposed.

Mailing Address: Texas Instruments, Post Office Box 655303, Dallas, Texas 75265 Copyright © 2025. Texas Instruments Incorporated